

45V PNP SMALL SIGNAL TRANSISTOR IN SOT523

Description

This Bipolar Junction Transistor (BJT) is designed to meet the stringent requirements of Automotive applications.

Features

- BV_{CEO} > -45V
- I_C = -100mA Collector Current
- Epitaxial Planar Die Construction
- Ultra-Small Surface Mount Package
- Complementary NPN Type: BC847BTQ
- Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)
- Qualified to AEC-Q101 Standards for High Reliability
- PPAP Capable (Note 4)

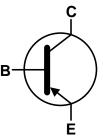
Mechanical Data

- Case: SOT523
- Case Material: Molded Plastic. "Green" Molding Compound.
 UL Flammability Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Finish Matte Tin Plated Leads
 Solderable per MIL-STD-202, Method 208 ³
- Weight: 0.002 grams (Approximate)

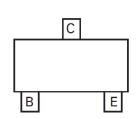
SOT523







Device Symbol



Pin-Out Top View

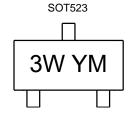
Ordering Information (Notes 4 and 5)

Part Number	Compliance	Marking	Reel Size (inches)	Tape Width (mm)	Quantity per Reel
BC857BTQ-7	Automotive	3W	7	8	3,000

Notes:

- 1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS) & 2011/65/EU (RoHS 2) compliant.
- 2. See http://www.diodes.com/quality/lead_free.html for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free
- 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
- 4. Automotive products are AEC-Q101 qualified and are PPAP capable. Refer to http://www.diodes.com/product_compliance_definitions.html.
- 5. For packaging details, go to our website at https://www.diodes.com/design/support/packaging/diodes-packaging/.

Marking Information



3W = Product Type Marking Code YM = Date Code Marking Y or \overline{Y} = Year (ex: E = 2017) M or \overline{M} = Month (ex: 9 = September)

Date Code Key

Year	201	7	2018	2019	2020	2021	2022	202	3 20	24	2025	2026	2027
Code	Е		F	G	Н	I	J	K	l	_	М	N	0
Month	1	Jai	n Fel	o Mar	Apr	May	Jun	Jul	Aug	Sep	Oct	Nov	Dec
Code		1	2	3	4	5	6	7	8	9	0	N	D



Absolute Maximum Ratings (@ $T_A = +25^{\circ}C$, unless otherwise specified.)

Characteristic	Symbol	Value	Unit
Collector-Base Voltage	V_{CBO}	-50	V
Collector-Emitter Voltage	V _{CEO}	-45	V
Emitter-Base Voltage	V _{EBO}	-5.0	V
Collector Current	Ic	-100	mA

Thermal Characteristics (@T_A = +25°C, unless otherwise specified.)

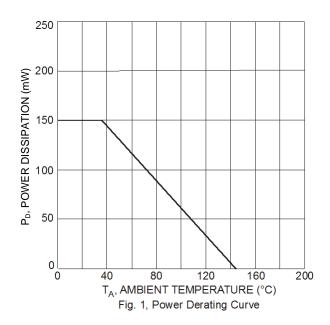
Characteristic	Symbol	Value	Unit
Power Dissipation (Note 6)	P _D	150	mW
Thermal Resistance, Junction to Ambient (Note 6)	$R_{ heta JA}$	833	°C/W
Operating and Storage Temperature Range	T _J , T _{STG}	-55 to +150	°C

ESD Ratings (Note 7)

Characteristic	Symbol	Value	Unit	JEDEC Class
Electrostatic Discharge – Human Body Model	ESD HBM	4,000	V	3A
Electrostatic Discharge – Machine Model	ESD MM	400	V	С

Notes:

Thermal Characteristics and Derating Information



^{6.} For a device mounted with the collector lead on minimum recommended pad layout 1oz copper that is on a single-sided 1.6mm FR-4 PCB; device is measured under still air conditions whilst operating in a steady-state.

^{7.} Refer to JEDEC specification JESD22-A114 and JESD22-A115.



Electrical Characteristics (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition
OFF CHARACTERISTICS (Note 8)	•					
Collector-Base Breakdown Voltage	BV _{CBO}	-50		_	V	$I_C = -10\mu A$
Collector-Emitter Breakdown Voltage	BV _{CEO}	-45	_		V	$I_C = -10mA$
Emitter-Base Breakdown Voltage	BV _{EBO}	-5	_	_	V	I _E = -10μA
ON CHARACTERISTICS (Note 8)	•					
DC Current Gain	h _{FE}	220	290	475	_	$V_{CE} = -5.0V, I_{C} = -2.0mA$
Collector-Emitter Saturation Voltage	M	_	_	-300	-300 -650 mV	I _C = -10mA, I _B = -0.5mA
Collector-Emitter Saturation voltage	V _{CE(SAT)}	_	_	-650		$I_C = -100 \text{mA}, I_B = -5.0 \text{mA}$
Base-Emitter Saturation Voltage	\/	_	-700	_	mV	$I_C = -10 \text{mA}, I_B = -0.5 \text{mA}$
base-Emilier Saturation voltage	V _{BE(SAT)}	_	-900			$I_C = -100 \text{mA}, I_B = -5.0 \text{mA}$
Base-Emitter Voltage	V	-600	_	-750	mV	$V_{CE} = -5.0V, I_{C} = -2.0mA$
base-Emitter voitage	V _{BE(ON)}	_	_	-820		$V_{CE} = -5.0V, I_{C} = -10mA$
Collector-Emitter Cutoff Current	lone	_	_	-15	nA	$V_{CB} = -30V$
	I _{CBO}	_	_	-4.0	μΑ	$V_{CB} = -30V, T_A = +150$ °C
SMALL SIGNAL CHARACTERISTICS						
Output Capacitance	Сово	_	_	4.5	pF	$V_{CB} = -10V, f = 1.0MHz$
Current Gain-Bandwidth Product	f⊤	100	_	_	MHz	$V_{CE} = -5.0V, I_{C} = -10mA,$ f = 100MHz
						$I_C = -0.2 \text{mA}, V_{CE} = -5.0 \text{V},$
Noise Figure	N _F	_	_	10	dB	$R_S = 2.0k\Omega$, $f = 1.0KHz$,
						BW = 200Hz

Note: 8. Measured under pulsed conditions. Pulse width \leq 300 μ s. Duty cycle \leq 2%.



Typical Electrical Characteristics (@T_A = +25°C, unless otherwise specified.)

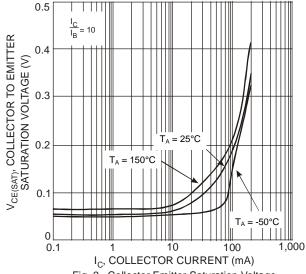
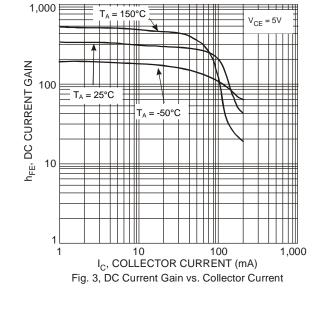


Fig. 2, Collector Emitter Saturation Voltage vs. Collector Current



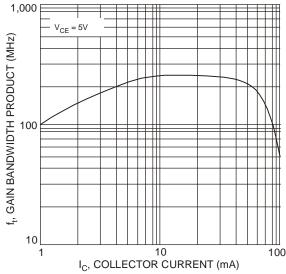


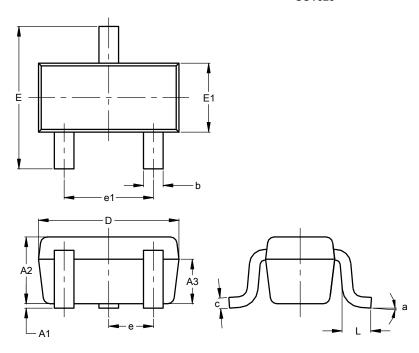
Fig. 4, Gain Bandwidth Product vs. Collector Current



Package Outline Dimensions

Please see http://www.diodes.com/package-outlines.html for the latest version.

SOT523

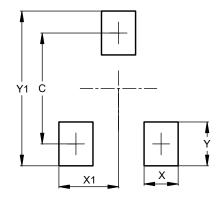


SOT523						
Dim	Min	Max	Тур			
A1	0.00	0.10	0.05			
A2	0.60	0.80	0.75			
A3	0.45	0.65	0.50			
b	0.15	0.30	0.22			
С	0.10	0.20	0.12			
D	1.50	1.70	1.60			
Е	1.45	1.75	1.60			
E1	0.75	0.85	0.80			
е		0.50 BS	С			
e1	0.90	1.10	1.00			
L	0.20	0.40	0.33			
а	0°		8°			
All Dimensions in mm						

Suggested Pad Layout

Please see http://www.diodes.com/package-outlines.html for the latest version.

SOT523



Dimensions	Value
С	1.29
Х	0.40
X1	0.70
Υ	0.51
Y1	1.80



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